# **BLC9H10XS-606A**

## **Power LDMOS transistor**

**AMPLEON** 

Rev. 1 — 24 March 2020

Product data sheet

### 1. Product profile

### 1.1 General description

600 W LDMOS packaged asymmetric Doherty power transistor for base station applications at frequencies from 616 MHz to 960 MHz.

#### Table 1. Typical performance 634.5/737 MHz

Typical RF performance at  $T_{case} = 25$  °C in an asymmetrical Doherty demo circuit.  $V_{DS} = 50$  V;  $I_{Dq} = 400$  mA (main);  $V_{GS(amp)peak} = 0.7$  V, unless otherwise specified.

Test signal	f	V <sub>DS</sub>	P <sub>L(AV)</sub>	G <sub>p</sub>	η <sub>D</sub>	ACPR
	(MHz)	(V)	(dBm)	(dB)	(%)	(dBc)
1-carrier W-CDMA	617 to 652	50	49.2	19.1	52.3	-33.5 [ <u>1][2]</u>
	728 to 746	50	49.2	19.5	50.2	-35 <u>[1][2]</u>

<sup>[1]</sup> Test signal: 1-carrier W-CDMA; 3GPP test model 1; 64 DPCH; PAR = 9.6 dB at 0.01 % probability on CCDF.

#### Table 2. Typical performance 789.5 MHz

Typical RF performance at  $T_{case} = 25$  °C in an asymmetrical Doherty demo circuit.  $V_{DS} = 48$  V;  $I_{Dq} = 500$  mA (main);  $V_{GS(amp)peak} = 0.05$  V, unless otherwise specified.

Test signal	f	$V_{DS}$	P <sub>L(AV)</sub>	G <sub>p</sub>	$\eta_{\mathbf{D}}$	ACPR
	(MHz)	(V)	(dBm)	(dB)	(%)	(dBc)
1-carrier W-CDMA	758 to 821	48	50.5	18.8	55.5	-29.3 [ <u>1]</u>

Test signal: 1-carrier W-CDMA; 3GPP test model 1; 64 DPCH; PAR = 9.6 dB at 0.01 % probability on CCDF.

#### Table 3. Typical performance 881.5 MHz

Typical RF performance at  $T_{case} = 25$  °C in an asymmetrical Doherty demo circuit.  $V_{DS} = 48$  V;  $I_{Dq} = 400$  mA (main);  $V_{GS(amp)peak} = 0.05$  V, unless otherwise specified.

Test signal	f	V <sub>DS</sub>	P <sub>L(AV)</sub>	Gp	η <sub>D</sub>	ACPR
	(MHz)	(V)	(dBm)	(dB)	(%)	(dBc)
1-carrier W-CDMA	869 to 894	48	50.5	17.9	53.2	-30.2 [ <u>1</u> ]

Test signal: 1-carrier W-CDMA; 3GPP test model 1; 64 DPCH; PAR = 9.6 dB at 0.01 % probability on CCDF.

### Table 4. Typical performance 942 MHz

Typical RF performance at  $T_{case} = 25$  °C in an asymmetrical Doherty demo circuit.  $V_{DS} = 48$  V;  $I_{Dq} = 350$  mA (main);  $V_{GS(amp)peak} = 0.05$  V, unless otherwise specified.

Test signal	f	V <sub>DS</sub>	P <sub>L(AV)</sub>	Gp	ηь	ACPR
	(MHz)	(V)	(dBm)	(dB)	(%)	(dBc)
1-carrier W-CDMA	925 to 960	48	50.5	17.2	54.7	-29.2 <sup>[1]</sup>

<sup>[1]</sup> Test signal: 1-carrier W-CDMA; 3GPP test model 1; 64 DPCH; PAR = 9.6 dB at 0.01 % probability on CCDF.

<sup>[2]</sup> Test data is based on wideband demo measurement (f = 617 MHz to 746 MHz).

### 1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent digital pre-distortion capability
- Internally matched for ease of use
- Integrated ESD protection
- For RoHS compliance see the product details on the Ampleon website

### 1.3 Applications

RF power amplifiers for base stations and multi carrier applications in the 616 MHz to 960 MHz frequency range

### 2. Pinning information

Table 5. Pinning

Pin	Description		Simplified outline	Graphic symbol
1	drain1			,
2	drain2			
3	gate1			3
4	gate2		3 4	5
5	source	[1]		2 sym117

<sup>[1]</sup> Connected to flange.

### 3. Ordering information

Table 6. Ordering information

Type number	Packag	nckage					
	Name	Description Version					
BLC9H10XS-606A	-	plastic earless flanged cavity package; 4 leads	SOT1250-4				

## 4. Limiting values

Table 7. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	110	V
V <sub>GS(amp)main</sub>	main amplifier gate-source voltage		-6	+11	V
V <sub>GS(amp)peak</sub>	peak amplifier gate-source voltage		-6	+11	V

BLC9H10XS-606A

Table 7. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C
T <sub>case</sub>	case temperature	[1]	-40	+150	°C

<sup>[1]</sup> Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

### 5. Thermal characteristics

Table 8. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-c)</sub>	thermal resistance from junction to case	$V_{DS}$ = 50 V; $I_{Dq}$ = 600 mA (main); $V_{GS(amp)peak}$ = 0.5 V; $T_{case}$ = 80 °C		
		P <sub>L</sub> = 112 W	0.236	K/W
		P <sub>L</sub> = 141 W	0.198	K/W

### 6. Characteristics

Table 9. DC characteristics

 $T_i = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Main dev	rice					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1.5 \text{ mA}$	110	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_D = 150 \text{ mA}$	1.5	2.0	2.5	٧
$V_{GSq}$	gate-source quiescent voltage	$V_{DS} = 47 \text{ V}; I_D = 600 \text{ mA}$	-	2	-	٧
I <sub>DSS</sub>	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}$	-	-	1.4	μΑ
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	24.5	-	Α
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V	-	-	140	nΑ
g <sub>fs</sub>	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 7.5 \text{ A}$	-	9.8	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 5.25 \text{ A}$	-	160	203	mΩ
Peak dev	rice					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 3 \text{ mA}$	110	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_D = 300 \text{ mA}$	1.5	2.0	2.5	V
$V_{GSq}$	gate-source quiescent voltage	$V_{DS} = 47 \text{ V}; I_D = 1200 \text{ mA}$	-	2	-	V
I <sub>DSS</sub>	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}$	-	-	2.8	μΑ
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	49.0	-	А
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V	-	-	280	nA
g <sub>fs</sub>	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 15.0 \text{ A}$	-	18.7	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 10.5 \text{ A}$	-	82	107	mΩ

#### Table 10. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH;  $f_1$  = 760.5 MHz;  $f_2$  = 800.5 MHz; RF performance at  $V_{DS}$  = 48 V;  $I_{Dq}$  = 550 mA (main);  $V_{GS(amp)peak}$  = 0.5 V;  $T_{case}$  = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 758 MHz to 803 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P <sub>L(AV)</sub> = 107 W	16.8	18	-	dB
RLin	input return loss	P <sub>L(AV)</sub> = 107 W	-	-13	-8	dB
$\eta_{D}$	drain efficiency	P <sub>L(AV)</sub> = 107 W	48	53.8	-	%
ACPR	adjacent channel power ratio	P <sub>L(AV)</sub> = 107 W	-	-31	-26	dBc

#### Table 11. RF characteristics

Test signal: pulsed CW,  $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %; f = 803 MHz; RF performance at  $V_{DS}$  = 48 V;  $I_{Dq}$  = 550 mA;  $V_{GS(amp)peak}$  = 0.5 V;  $T_{case}$  = 25 °C; unless otherwise specified; in a Doherty production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
P <sub>L(3dB)</sub>	output power at 3 dB gain compression	-	485	630	-	W

### 7. Test information

### 7.1 Ruggedness in Doherty operation

The BLC9H10XS-606A is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS}$  = 48 V;  $I_{Dq}$  = 550 mA;  $V_{GS(amp)peak}$  = 0.5 V; f = 758 MHz;  $P_L$  = 200 W (5 dB OBO); 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH.

### 7.2 Impedance information

Table 12. Typical impedance of main device

Measured load-pull data of main device;  $I_{Dq} = 900$  mA (main);  $V_{DS} = 48$  V; pulsed CW ( $t_p = 100 \ \mu s$ ;  $\delta = 10 \ \%$ ).

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [2]	G <sub>p</sub> [2]
(MHz)	<b>(</b> Ω <b>)</b>	<b>(</b> Ω <b>)</b>	(W)	(%)	(dB)
Maximum	n power load				
780	4.3 – j4.5	1.6 + j0.2	304	66.0	19.1
800	4.4 – j4.9	1.6 + j0.2	303	64.7	19.1
820	4.6 – j5.3	1.6 + j0.2	303	65.0	19.2
840	4.7 – j5.6	1.6 + j0.2	308	65.6	19.1
Maximun	Maximum drain efficiency load				
780	4.3 – j4.5	2.0 + j1.0	244	70.7	20.8
800	4.4 – j4.9	1.4 + j1.0	233	70.1	20.7
820	4.6 – j5.3	1.4 + j1.2	209	72.2	21.2
840	4.7 – j5.6	1.4 + j1.2	206	72.5	21.2

<sup>[1]</sup>  $Z_S$  and  $Z_L$  defined in Figure 1.

<sup>[2]</sup> At 3 dB gain compression.

Table 13. Typical impedance of peak device

Measured load-pull data of peak device;  $I_{Dq}$  = 1800 mA (peak);  $V_{DS}$  = 48 V; pulsed CW ( $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %).

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [2]	G <sub>p</sub> [2]
(MHz)	<b>(</b> Ω <b>)</b>	<b>(</b> Ω <b>)</b>	(W)	(%)	(dB)
Maximun	n power load				
780	2.5 – j2.8	1.0 – j0.1	620	65.7	17.8
800	2.5 – j3.0	1.0 – j0.1	633	65.9	17.8
820	2.7 – j3.2	1.0 – j0.1	631	64.8	17.6
840	2.7 – j3.3	1.0 – j0.1	639	64.8	17.7
Maximun	Maximum drain efficiency load				
780	2.5 – j2.8	0.6 + j0.6	371	75.6	20.5
800	2.5 – j3.0	0.6 + j0.6	375	78.8	20.8
820	2.7 – j3.2	0.6 + j0.4	447	77.9	19.5
840	2.7 – j3.3	0.6 + j0.4	447	77.2	19.8

<sup>[1]</sup>  $Z_S$  and  $Z_L$  defined in Figure 1.

[2] At 3 dB gain compression.

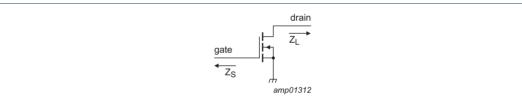
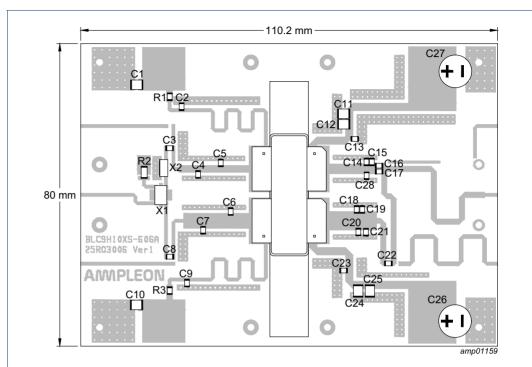


Fig 1. Definition of transistor impedance

### 7.3 Test circuit



Printed-Circuit Board (PCB): RO3006:  $\epsilon_r$  = 6.15; thickness = 0.635 mm; thickness copper plating = 35  $\mu$ m. See Table 14 for a list of components.

Fig 2. Component layout

**Table 14.** List of components
See Figure 2 for component layout.

Component	Description	Value	Remarks
C1, C10	multilayer ceramic chip capacitor	10 μF, 50 V	Murata: Hi-Q SMD 1210
C2, C3, C8, C9, C13, C22, C23	multilayer ceramic chip capacitor	68 pF	Murata: Hi-Q SMD 0805
C4	multilayer ceramic chip capacitor	3.9 pF	Murata: Hi-Q SMD 0805
C5, C15	multilayer ceramic chip capacitor	4.7 pF	Murata: Hi-Q SMD 0805
C6, C7	multilayer ceramic chip capacitor	5.6 pF	Murata: Hi-Q SMD 0805
C11, C12, C24, C25	multilayer ceramic chip capacitor	10 μF, 100 V	Murata: Hi-Q SMD 1210
C14	multilayer ceramic chip capacitor	4.3 pF	Murata: Hi-Q SMD 0805
C16, C17, C18	multilayer ceramic chip capacitor	5.1 pF	Murata: Hi-Q SMD 0805
C19, C28	multilayer ceramic chip capacitor	6.2 pF	Murata: Hi-Q SMD 0805
C20	multilayer ceramic chip capacitor	1 pF	Murata: Hi-Q SMD 0805
C21	multilayer ceramic chip capacitor	10 pF	Murata: Hi-Q SMD 0805
C26, C27	electrolytic capacitor	1000 μF, 100 V	
R1, R3	resistor	5.1 Ω	SMD 0805
R2	resistor	50 Ω	SMD 2512
X1	hybrid coupler	2 dB, 90°	X3C7F1-02S
X2	attenuator	1 dB; 10 W	D10AA1Z4

### 7.4 Graphical data

### 7.4.1 Pulsed CW

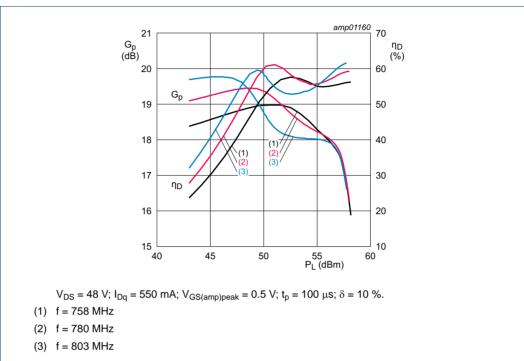
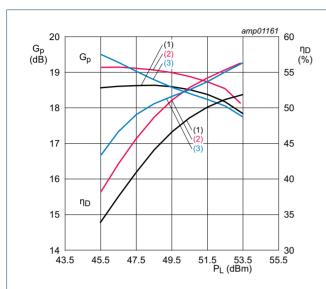


Fig 3. Power gain and drain efficiency as function of output power; typical values

### 7.4.2 1-Carrier W-CDMA

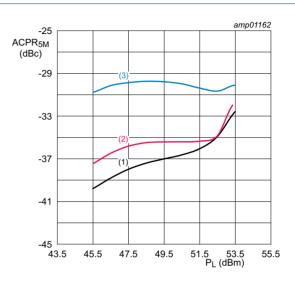
Test signal: 1-carrier W-CDMA; PAR = 7.2 dB per carrier at 0.01 % probability on CCDF; 3GPP test model 1; 1 to 64 DPCH.



 $V_{DS} = 48 \text{ V}$ ;  $I_{Dq} = 550 \text{ mA}$ ;  $V_{GS(amp)peak} = 0.5 \text{ V}$ .

- (1) f = 760.5 MHz
- (2) f = 780 MHz
- (3) f = 800.5 MHz

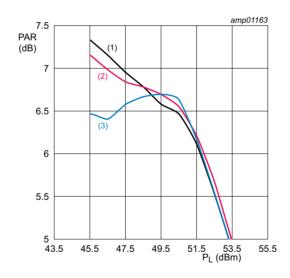
Fig 4. Power gain and drain efficiency as function of output power; typical values



 $V_{DS} = 48 \text{ V}; I_{Dq} = 550 \text{ mA}; V_{GS(amp)peak} = 0.5 \text{ V}.$ 

- (1) f = 760.5 MHz
- (2) f = 780 MHz
- (3) f = 800.5 MHz

Fig 5. Adjacent channel power ratio (5 MHz) as a function of output power; typical values



 $V_{DS} = 48 \text{ V}; I_{Dq} = 550 \text{ mA}; V_{GS(amp)peak} = 0.5 \text{ V}.$ 

- (1) f = 760.5 MHz
- (2) f = 780 MHz
- (3) f = 800.5 MHz

Fig 6. Peak-to-average power ratio as a function of output power; typical values

### 8. Package outline

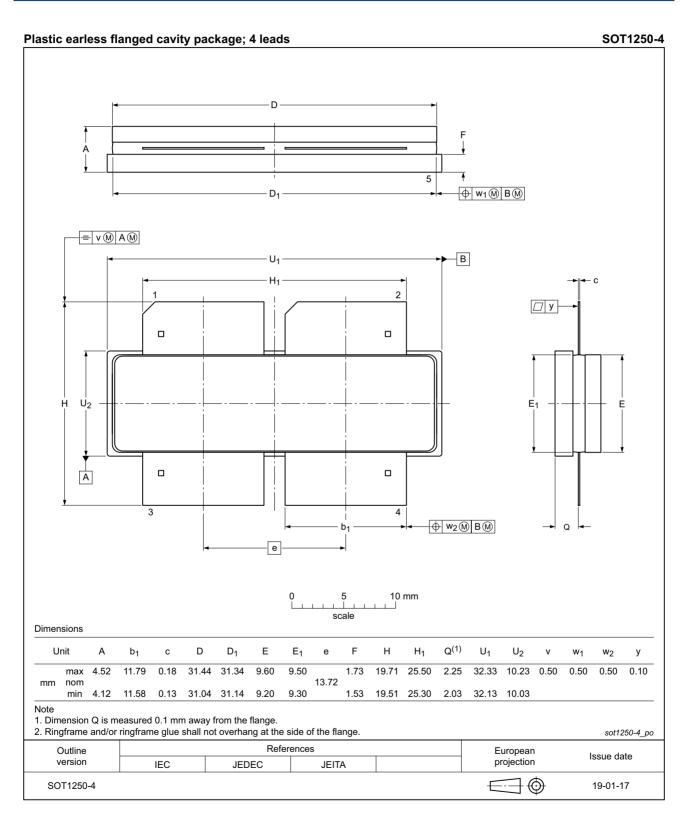


Fig 7. Package outline SOT1250-4

### 9. Handling information

#### **CAUTION**



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 15. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C3 [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

- [1] CDM classification C3 is granted to any part that passes after exposure to an ESD pulse of  $\geq$  1000 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V.

### 10. Abbreviations

Table 16. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MTF	Median Time to Failure
ОВО	Output Back Off
PAR	Peak-to-Average Ratio
RoHS	Restriction of Hazardous Substances
SMD	Surface Mounted Device
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

## 11. Revision history

Table 17. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC9H10XS-606A v.1	20200324	Product data sheet	-	-

### 12. Legal information

### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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BLC9H10XS-606A

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### 13. Contact information

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# **BLC9H10XS-606A**

### **Power LDMOS transistor**

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